

# NDF04N60Z, NDD04N60Z

## N-Channel Power MOSFET 600 V, 2.0 Ω

### Features

- Low ON Resistance
- Low Gate Charge
- ESD Diode-Protected Gate
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Symbol	NDF	NDD	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	600		V
Continuous Drain Current R <sub>θJC</sub> (Note 1)	I <sub>D</sub>	4.8	4.1	A
Continuous Drain Current R <sub>θJC</sub> , T <sub>A</sub> = 100°C (Note 1)	I <sub>D</sub>	3.0	2.6	A
Pulsed Drain Current, V <sub>GS</sub> @ 10V	I <sub>DM</sub>	20	20	A
Power Dissipation R <sub>θJC</sub>	P <sub>D</sub>	30	83	W
Gate-to-Source Voltage	V <sub>GS</sub>	±30		V
Single Pulse Avalanche Energy, I <sub>D</sub> = 4.0 A	E <sub>AS</sub>	120		mJ
ESD (HBM) (JESD22-A114)	V <sub>esd</sub>	3000		V
RMS Isolation Voltage (t = 0.3 sec., R.H. ≤ 30%, T <sub>A</sub> = 25°C) (Figure 15)	V <sub>ISO</sub>	4500	-	V
Peak Diode Recovery (Note 2)	dV/dt	4.5		V/ns
MOSFET dV/dt	dV/dt	60		V/ns
Continuous Source Current (Body Diode)	I <sub>S</sub>	4.0		A
Maximum Temperature for Soldering Leads	T <sub>L</sub>	260		°C
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

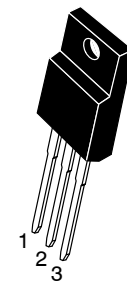
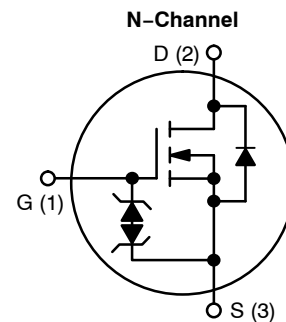
1. Limited by maximum junction temperature
2. I<sub>SD</sub> = 4.0 A, di/dt ≤ 100 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, T<sub>J</sub> = +150°C



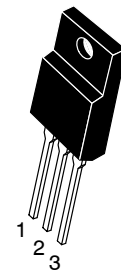
ON Semiconductor®

<http://onsemi.com>

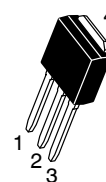
V <sub>DSS</sub> (@ T <sub>Jmax</sub> )	R <sub>DS(on)</sub> (MAX) @ 2 A
650 V	2.0 Ω



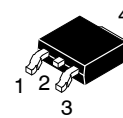
NDF04N60ZG  
TO-220FP  
CASE 221D



NDF04N60ZH  
TO-220FH  
CASE 221AH



NDD04N60Z-1G  
IPAK  
CASE 369D



NDD04N60ZT4G  
DPAK  
CASE 369AA

### ORDERING AND MARKING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

# NDF04N60Z, NDD04N60Z

## THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	NDF04N60Z NDD04N60Z	4.2	°C/W
		1.5	
Junction-to-Ambient Steady State	(Note 3) NDF04N60Z (Note 4) NDD04N60Z (Note 3) NDD04N60Z-1	50	
		38	
		80	

3. Insertion mounted

4. Surface mounted on FR4 board using 1" sq. pad size (Cu area = 1.127 in sq [2 oz] including traces).

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	BV <sub>DSS</sub>	600			V
Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> = 1 mA	ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>		0.6		V/°C
Drain-to-Source Leakage Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	I <sub>DSS</sub>	25°C		1	μA
			150°C		50	
Gate-to-Source Forward Leakage	V <sub>GS</sub> = ±20 V	I <sub>GSS</sub>			±10	μA

### ON CHARACTERISTICS (Note 5)

Static Drain-to-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.0 A	R <sub>DS(on)</sub>		1.8	2.0	Ω
Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50 μA	V <sub>GS(th)</sub>	3.0	3.9	4.5	V
Forward Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 2.0 A	g <sub>FS</sub>		3.3		S

### DYNAMIC CHARACTERISTICS

Input Capacitance (Note 6)	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	C <sub>iss</sub>	427	535	640	pF
Output Capacitance (Note 6)		C <sub>oss</sub>	50	62	75	
Reverse Transfer Capacitance (Note 6)		C <sub>rss</sub>	8	14	20	
Total Gate Charge (Note 6)	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 4.0 A, V <sub>GS</sub> = 10 V	Q <sub>g</sub>	10	19	29	nC
Gate-to-Source Charge (Note 6)		Q <sub>gs</sub>	2	3.9	6	
Gate-to-Drain ("Miller") Charge		Q <sub>gd</sub>	5	10	15	nC
Plateau Voltage		V <sub>GP</sub>		6.5		V
Gate Resistance		R <sub>g</sub>		4.7		Ω

### RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 4.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 5 Ω	t <sub>d(on)</sub>		13		ns
Rise Time		t <sub>r</sub>		9.0		
Turn-Off Delay Time		t <sub>d(off)</sub>		24		
Fall Time		t <sub>f</sub>		15		

### SOURCE-DRAIN DIODE CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Diode Forward Voltage	I <sub>S</sub> = 4.0 A, V <sub>GS</sub> = 0 V	V <sub>SD</sub>			1.6	V
Reverse Recovery Time	V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 30 V I <sub>S</sub> = 4.0 A, di/dt = 100 A/μs	t <sub>rr</sub>		285		ns
Reverse Recovery Charge		Q <sub>rr</sub>		1.3		μC

5. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

6. Guaranteed by design.

# NDF04N60Z, NDD04N60Z

## TYPICAL CHARACTERISTICS

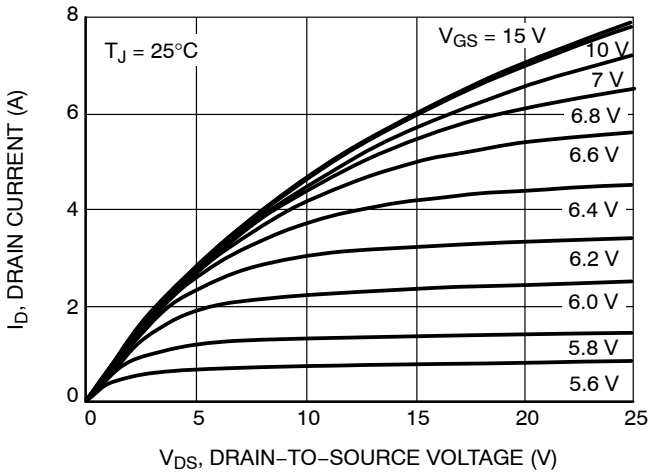


Figure 1. On-Region Characteristics

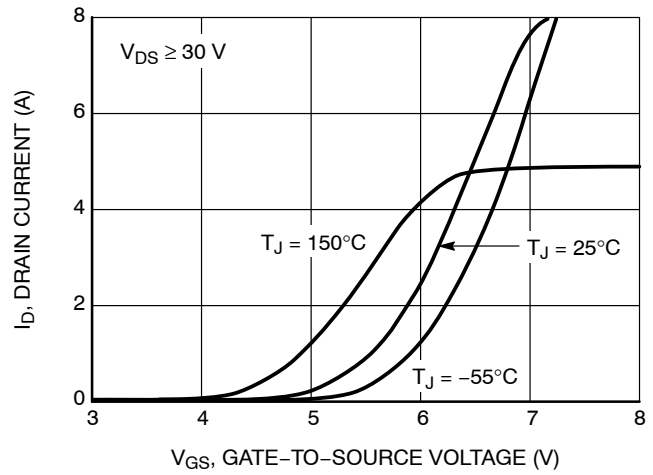


Figure 2. Transfer Characteristics

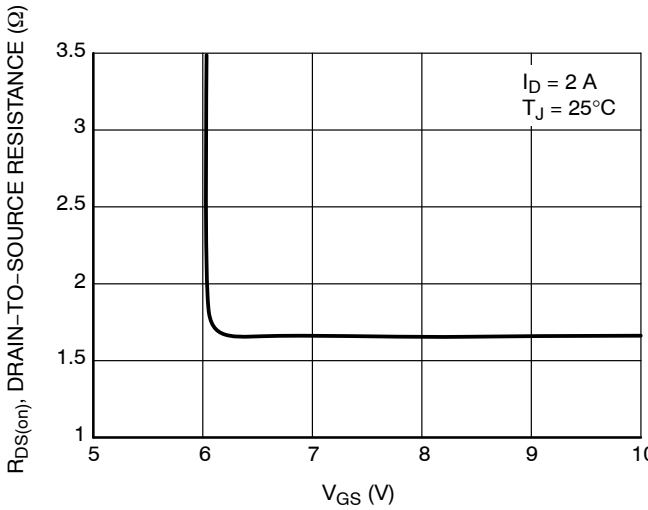


Figure 3. On-Resistance vs. Gate Voltage

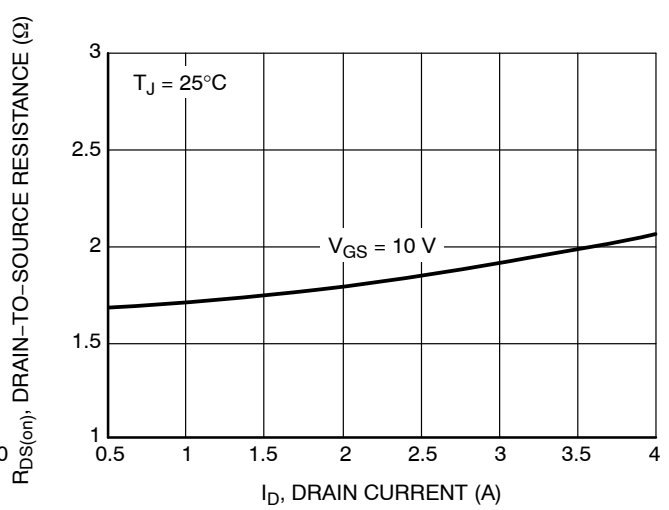


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

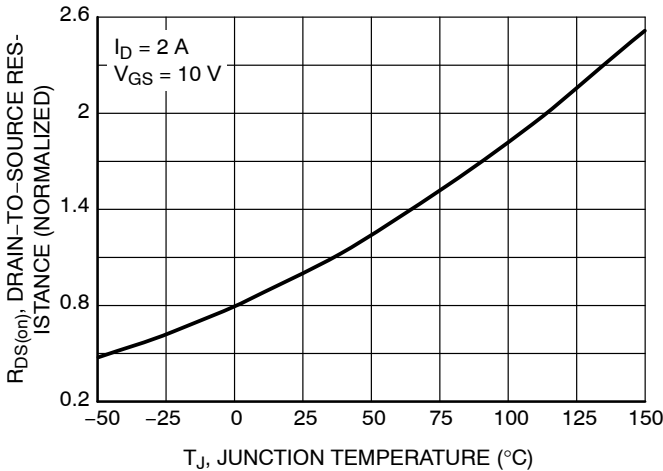


Figure 5. On-Resistance Variation with Temperature

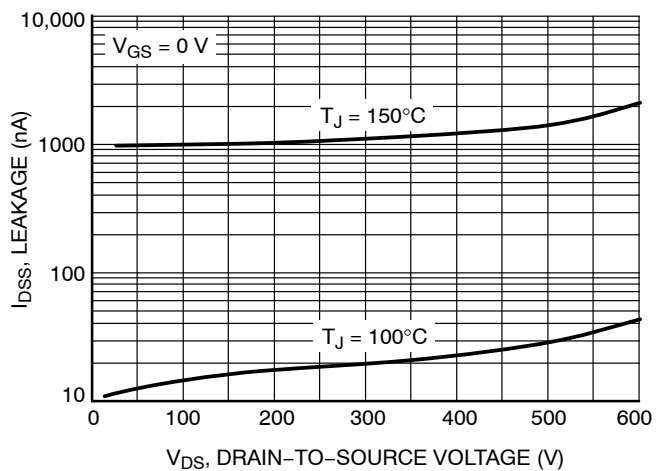


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NDF04N60Z, NDD04N60Z

## TYPICAL CHARACTERISTICS

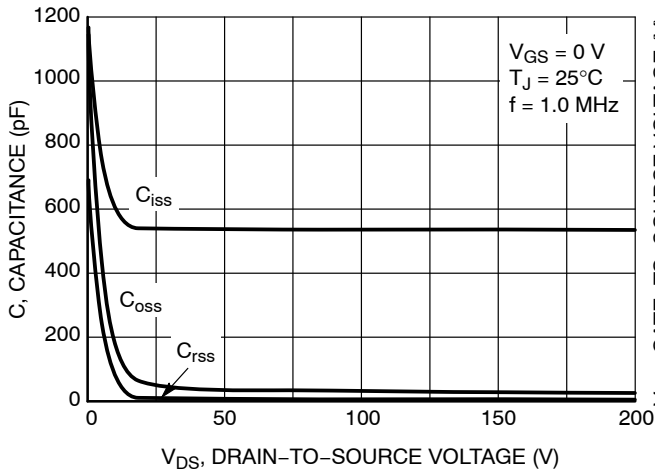


Figure 7. Capacitance Variation

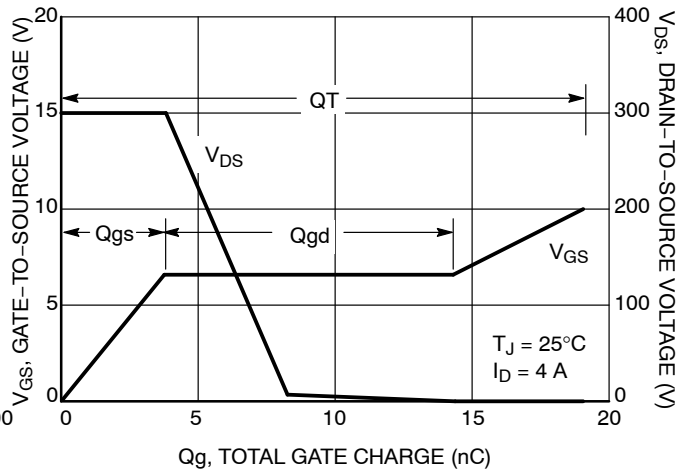


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

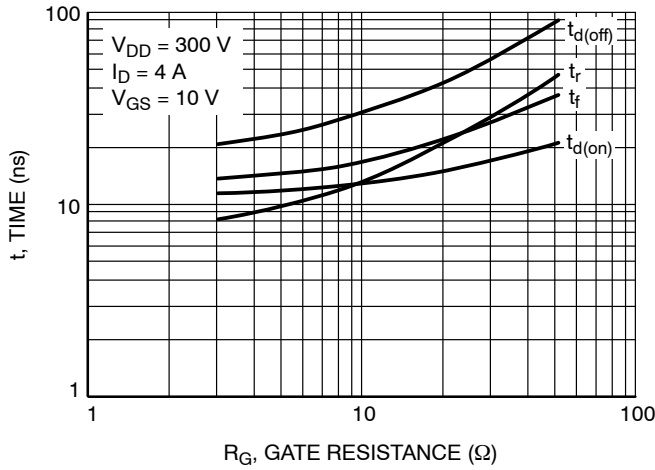


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

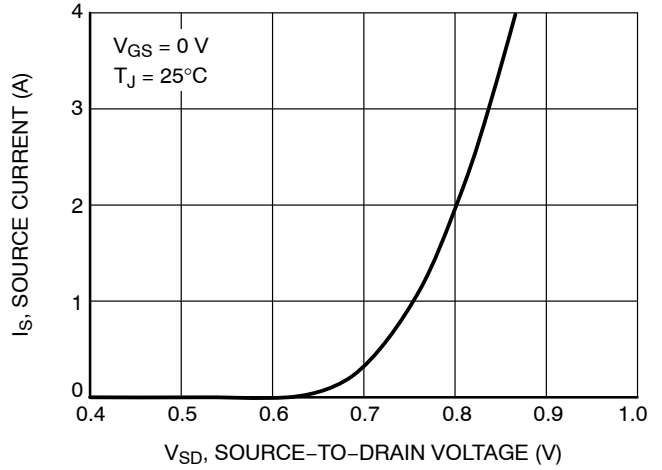


Figure 10. Diode Forward Voltage vs. Current

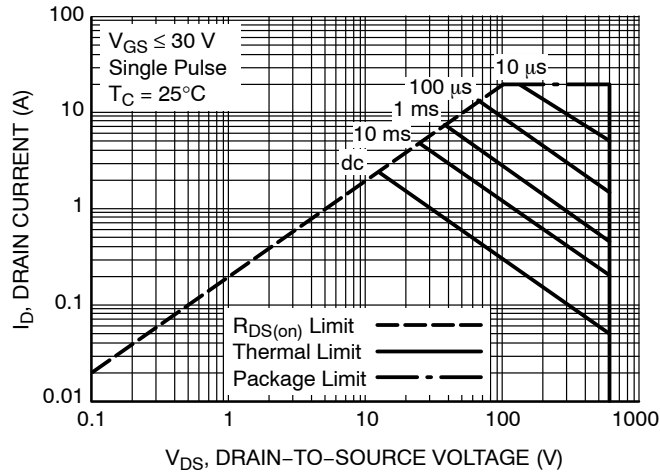


Figure 11. Maximum Rated Forward Biased Safe Operating Area for NDF04N60Z

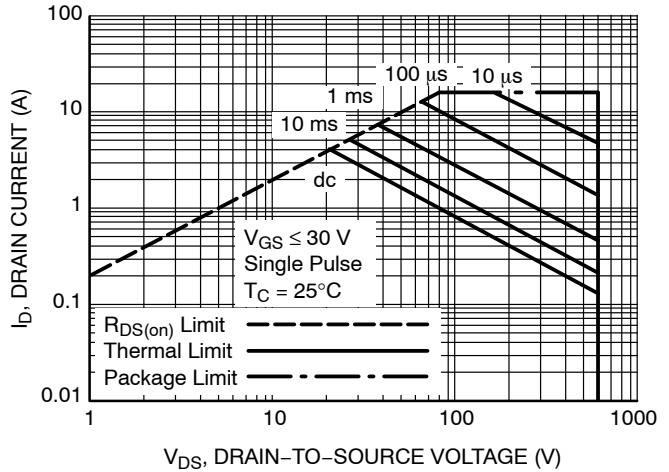


Figure 12. Maximum Rated Forward Biased Safe Operating Area for NDD04N60Z

# NDF04N60Z, NDD04N60Z

## TYPICAL CHARACTERISTICS

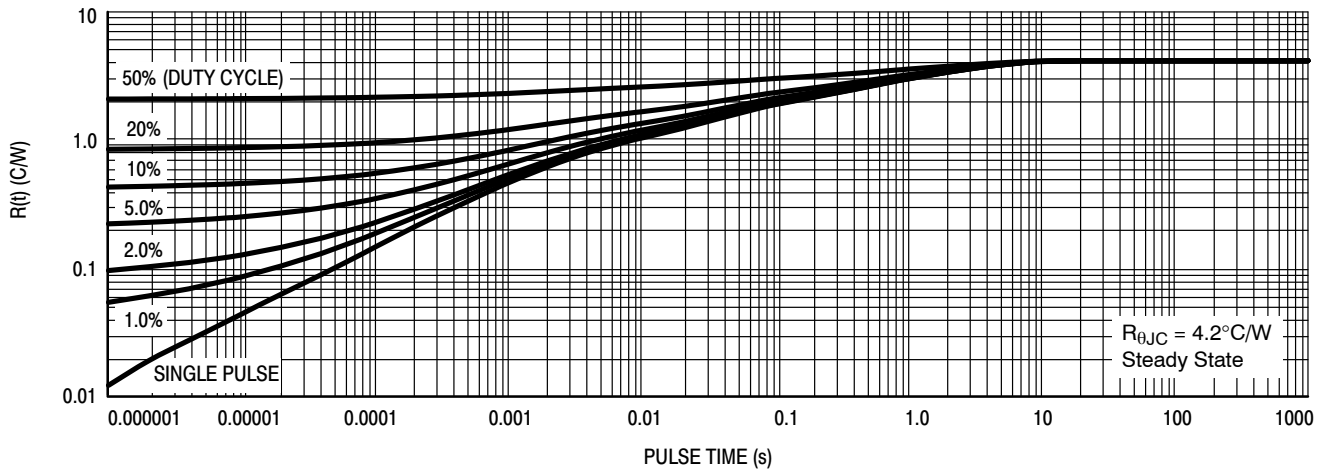


Figure 13. Thermal Impedance for NDF04N60Z

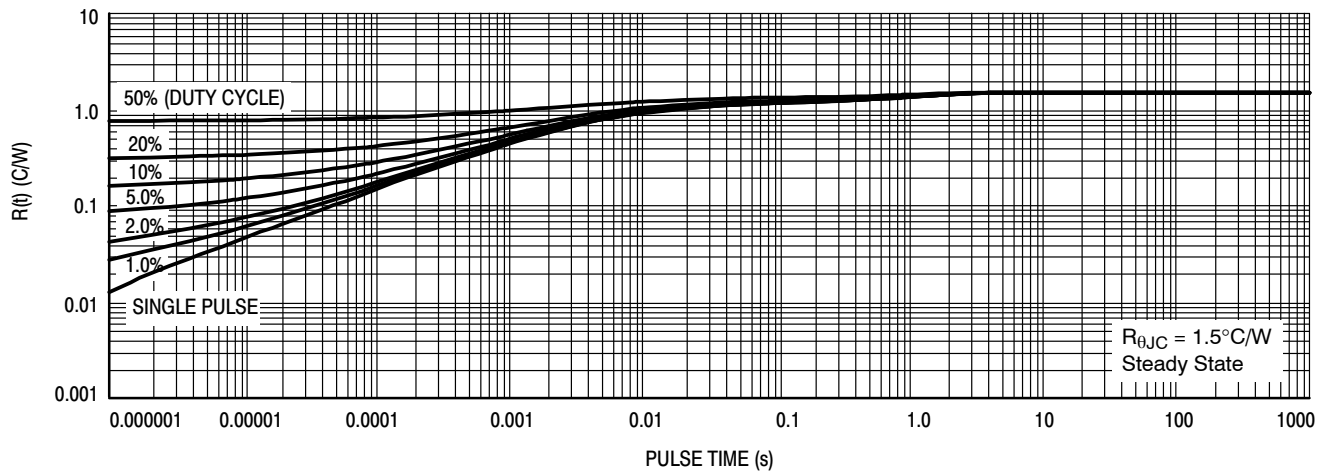


Figure 14. Thermal Impedance for NDD04N60Z

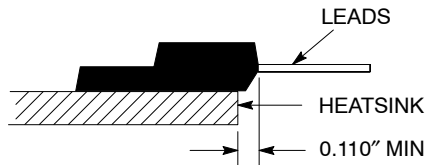


Figure 15. Mounting Position for Isolation Test

Measurement made between leads and heatsink with all leads shorted together.

\*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

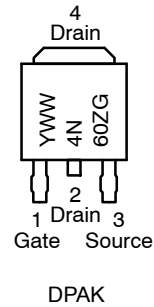
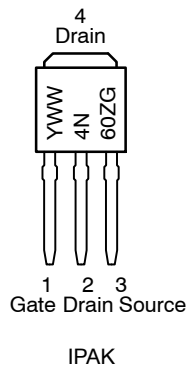
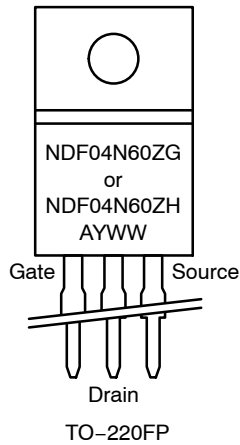
# NDF04N60Z, NDD04N60Z

## ORDERING INFORMATION

Order Number	Package	Shipping†
NDF04N60ZG	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail
NDF04N60ZH	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail
NDD04N60Z-1G	IPAK (Pb-Free, Halogen-Free)	75 Units / Rail
NDD04N60ZT4G	DPAK (Pb-Free, Halogen-Free)	2500 / Tape and Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MARKING DIAGRAMS

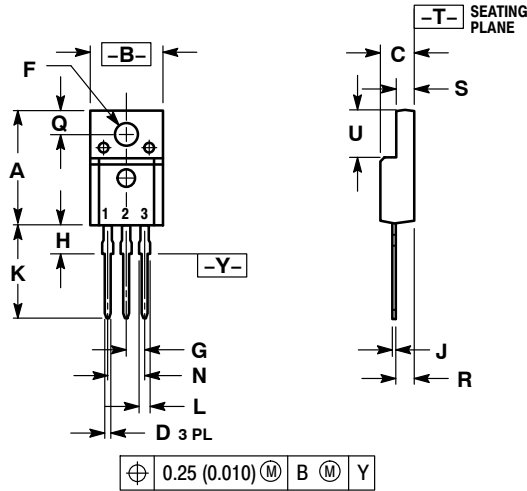


A = Location Code  
 Y = Year  
 WW = Work Week  
 G, H = Pb-Free, Halogen-Free Package

# NDF04N60Z, NDD04N60Z

## PACKAGE DIMENSIONS

### TO-220 FULLPAK CASE 221D-03 ISSUE K

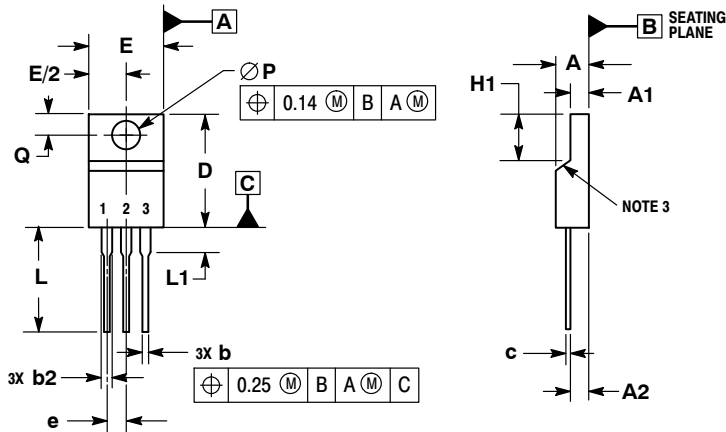


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH
  3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

- STYLE 1:
1. GATE
  2. DRAIN
  3. SOURCE

### TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE D



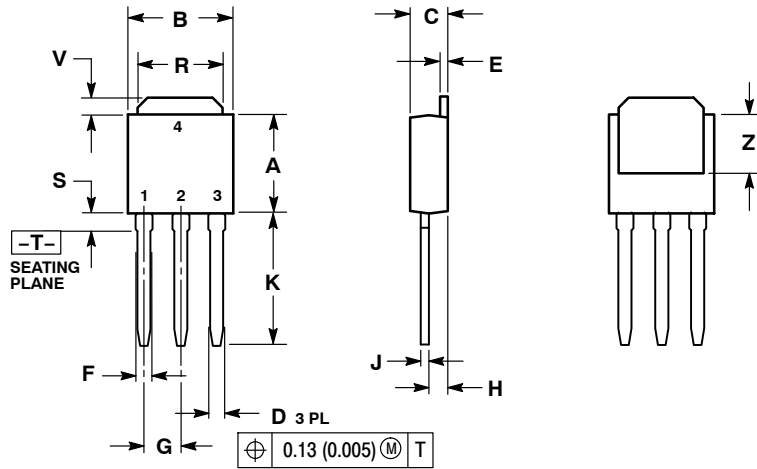
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR UNCONTROLLED IN THIS AREA.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
  5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

DIM	MILLIMETERS	
	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.70
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.70	7.10
L	12.70	14.73
L1	---	2.10
P	3.00	3.40
Q	2.80	3.20

# NDF04N60Z, NDD04N60Z

## PACKAGE DIMENSIONS

IPAK  
CASE 369D  
ISSUE C



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

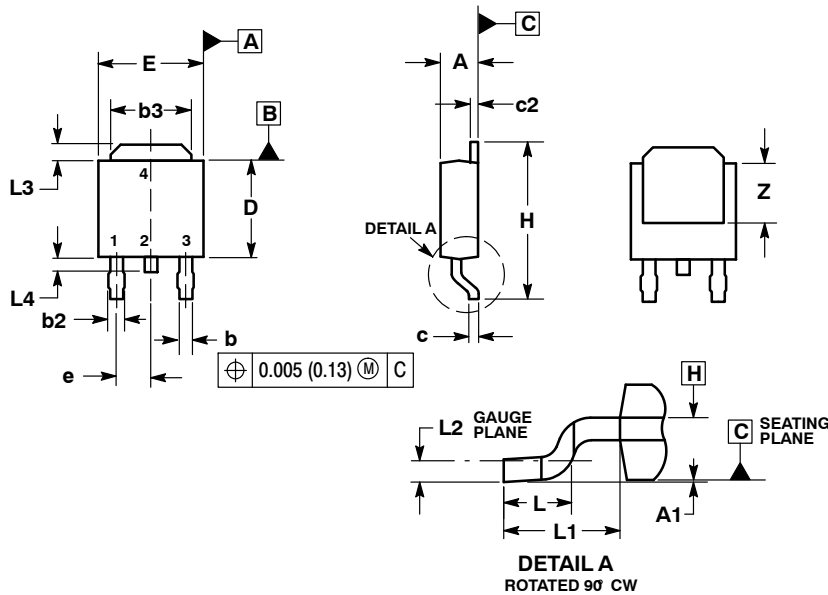
- STYLE 2:  
 PIN 1. GATE  
 2. DRAIN  
 3. SOURCE  
 4. DRAIN



# NDF04N60Z, NDD04N60Z

## PACKAGE DIMENSIONS

### DPAK (SINGLE GAUGE) CASE 369AA ISSUE B

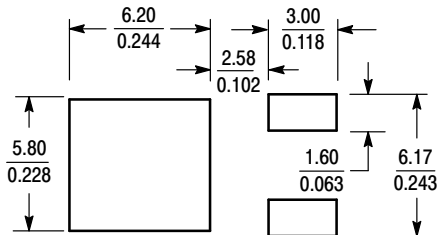


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

#### SOLDERING FOOTPRINT\*



SCALE 3:1  $\left(\frac{\text{mm}}{\text{inches}}\right)$

#### STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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